



<b>INFORMATION DISCLOSURE CITATION</b> PTO-1449		Customer Number: <b>26615</b>	ATTORNEY'S DKT No. H1420		APPLICATION No. <del>Unassigned</del> 10/75459	
			APPLICANT(S) Shibly S. Ahmed et al.			
			FILING DATE January 12, 2004		GROUP Unassigned 2818	
<b>U.S. PATENT DOCUMENTS</b>						
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
R	6,583,469	06-24-03	Fried et al.	257	329	01-28-02
J	6,562,665	05-13-03	Yu	438	149	10-16-00
J	6,551,886	04-22-03	Yu	438	300	04-27-01
<b>FOREIGN PATENT DOCUMENTS</b>						
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation Yes No
R	WO 03/015182	02-03	WIPO			
<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)</b>						
R	Digh Hisamoto et al., "FinFET-A Self-Aligned Double-Gate MOSFET Scalable to 20 nm," IEEE Transactions on Electron Devices, Vol. 47, No. 12, December 2000, pages 2320-2325.					
R	Yang-Kyu Choi et al., "Sub-20nm CMOS FinFET Technologies," 2001 IEEE, IEDM, pages 421-424.					
J	Xuejue Huang et al., "Sub-50 nm P-Channel FinFET," IEEE Transactions on Electron Devices, Vol. 48, No. 5, May 2001, pages 880-886.					
J	Xuejue Huang et al., "Sub 50-nm FinFET: PMOS," 1999 IEEE, IEDM, pages 67-70.					
J	Yang-Kyu Choi et al., "Nanoscale CMOS Spacer FinFET for the Terabit Era," IEEE Electron Device Letters, Vol. 23, No. 1, January 2002, pages 25-27.					
J	Co-pending U.S. Application No. 10/320,536 filed December 17, 2002 entitled: "FinFET Gate Formation Using Reverse Trim of Dummy Gate," 14 page specification, 11 sheets of drawings.					
J	Co-pending U.S. Application No. 10/459,589 filed June 12, 2003 entitled: "FinFET Gate Formation Using Reverse Trim and Oxide Polish," 17 page specification, 28 sheets of drawings.					
J	Co-pending U.S. Application No. 10/310,777 filed December 6, 2002 entitled: "Damascene Gate Process with Sacrificial Oxide in Semiconductor Devices," 19 page specification, 10 sheets of drawings.					
J	Co-pending U.S. Application No. 10/645,577 filed August 22, 2003 entitled: "Sacrificial Oxide Protection During Dummy Gate Removal in Damascene Gate Process in Semiconductor Devices," 19 page specification, 9 sheets of drawings.					
EXAMINER			DATE CONSIDERED			
						

<b>INFORMATION DISCLOSURE CITATION</b> PTO-1449		Customer Number: <b>26615</b>	ATTORNEY'S DKT No. H1420		APPLICATION No. Unassigned 10/154,559	
			APPLICANT(S) Shibly S. Ahmed et al.			
			FILING DATE January 12, 2004		GROUP Unassigned	

U.S. PATENT DOCUMENTS						
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
R	6,551,885	04-22-03	Yu	438	300	02-09-01
R	6,525,403	02-25-03	Inaba et al.	257	618	09-24-01
R	6,515,320	02-04-03	Azuma et al.	257	288	11-08-01
R	6,475,890	11-05-02	Yu	438	574	02-12-01
R	6,458,662	10-01-02	Yu	438	286	04-04-01
R	6,413,802	07-02-02	Hu et al.	438	151	10-23-00
R	6,406,951	06-18-02	Yu	438	183	02-12-01
R	6,342,410	01-29-02	Yu	438	164	07-10-00
R	6,303,447	10-16-01	Chhagan et al.	438	299	02-11-00
R	6,265,256	07-24-01	An et al.	438	201	09-17-98
R	5,960,270	09-28-99	Misra et al.	438	197	08-11-97
R	US2003/01581077	08-14-03	Mathew et al.	257	250	02-13-02
R	US2003/0141525	07-31-03	Nowak	257	288	02-05-03
R	US2003/0113970	06-19-03	Fried et al.	438	286	12-14-01
R	US2003/0111686	06-19-03	Nowak	257	328	12-13-01

FOREIGN PATENT DOCUMENTS							
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No

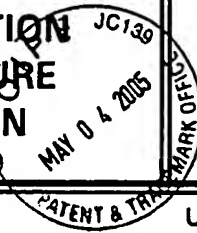
  

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)	

EXAMINER	DATE CONSIDERED <u>7/16/05</u>
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<b>INFORMATION DISCLOSURE CITATION</b> PTO-1449		<b>CUSTOMER NUMBER</b>  45114		ATTORNEY'S DKT No. H1420		APPLICATION No. 10/754,559	
				APPLICANT(S) Shibly S. Ahmed et al.			
				FILING DATE January 12, 2004		GROUP 2812	


**U.S. PATENT DOCUMENTS**

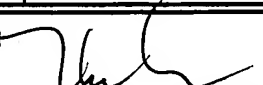
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
RL	6,764,884 B1	07/20/04	Yu et al.	438	157	
	6,465,823	10/15/02	Yagishita et al.	257	288	
	6,765,303 B1	07/20/04	Krivokapic et al.	257	903	
	6,509,611 B1	1/21/03	Park et al.	257	330	
	2002/0177263 A1	11/28/02	Hanafi et al.	438	183	
↓	2002/0153587 A1	10/24/02	Adkisson et al.	257	510	

**FOREIGN PATENT DOCUMENTS**

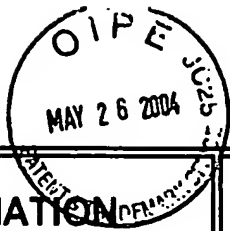
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No
RL	EP 1 383 164 A1	01/21/04	Europe				

**OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)**

RL	Copy of International Search Report dated March 4, 2005

EXAMINER 	DATE CONSIDERED 7/16/05
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant(s).



<b>INFORMATION DISCLOSURE CITATION</b> PTO-1449	<b>CUSTOMER NUMBER</b>  26615	ATTORNEY'S DKT No. H1420	APPLICATION NO. 10/754,559
		APPLICANT(s) Shibly S. Ahmed et al.	
		FILING DATE January 12, 2004	GROUP 2812

**U.S. PATENT DOCUMENTS**


EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
TL	6,396,108	05/28/02	Krivokapic et al.	257	365	
TL	5,801,397	09/01/98	Cunningham	257	66	

**FOREIGN PATENT DOCUMENTS**

EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No

**OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)**

TL	Stephen H. Tang et al., "Comparison of Short-Channel Effect and Offstate Leakage in Symmetric vs. Asymmetric Double Gate MOSFETs", IEEE International SOI Conference, October 2000, pp. 120-121
TL	Co-pending U.S. Application No. 10/720,166 filed November 25, 2003 entitled: "Damascene Gate Process with Sacrificial Oxide in Semiconductor"; 19 page specification, 10 sheets of drawings.
TL	Co-pending U.S. Application No. 10/838,228 filed May 5, 2004 entitled: "Sacrificial Oxide for Minimizing Box Undercut in Damascene FinFet"; 15 page specification, 12 sheets of drawings.
TL	United States Patent Application Publication No. US2002/0153587; publication date October 24, 2002; Adkisson et al.

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**U.S. PATENT DOCUMENTS**

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
<i>W</i>	6,645,797 B1	11/2003	Buynoski et al.	438	157	

**FOREIGN PATENT DOCUMENTS**

EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No

**OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)**


EXAMINER <i>Wash</i>	DATE CONSIDERED <i>7/16/05</i>
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